## **AMENDMENTS TO THE CLAIMS**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

## **Listing of Claims:**

1. (Currently Amended) A device for carrying outtreating a surface of a substrate in a plasma enhanced process, the device comprising:

within-a vacuum chamber, and

arranged in the vacuum chamber, a magnetron electrode (32), a positioning means substrate support (26), and a gas supply means gas supply lines (33),

wherein the magnetron electrode comprising of the unbalanced type and comprises a flat magnetron face (20) with peripheral and central magnetic poles of opposite polarities and further comprising means for producing a high frequency alternating electric field an electrode piece (21) being powered by a high frequency alternating voltage,

wherein the positioning means substrate support (26) being is electrically grounded or floating or negatively biased and equipped for positioning athe substrate (25) with a surface to be treated facing the magnetron face (20) at a distance thereof, and

wherein the gas supply means beinggas supply lines (33) are equipped for supplying a process gas or process gas mixture to the space between the magnetron face (20) and the surface to be treated of the substrate positioned on the

Application No.: 10/529531 Amendment Dated: April 25, 2007 Reply to Office action of: January 25, 2007

substrate support, and

wherein the magnetron electrode (32) is of the unbalanced type and that a

distance between the magnetron face (20) and the positioning means substrate

support (26) is adapted to the magnetic field created by the magnetron electrode

(32) such that there is a visible plasma band running between darker tunnels (11)

formed by magnetic field lines (10) extending between peripheral and central

magnetic poles of the magnetron face (20) and the surface to be treated, the plasma

band having a minimum width but having towards the surface to be treated a

homogeneous brightness.

2. (Previously Presented) The device according to claim 1, wherein a distance (A-

C) between the surface to be treated and the magnetron face (20) is at least 2%

larger than a visible height (A-B) of the tunnels (11).

3. (Previously Presented) The device according to claim 1, wherein a distance (A-

C) between the surface to be treated and the magnetron face (20) is at the most

20% larger than a visible height (A-B) of the tunnels (11).

4. (Previously Presented) The device according to claim 1, wherein a magnetic

strength of the central magnetic pole of the magnetron face (20) is about half of a

magnetic strength of the peripheral pole.

5. (Previously Presented) The device according to claim 1, wherein the magnetron

electrode (32) comprises an electrode element (21) being connected to a source of

Page 3 of 11

Application No.: 10/529531 Amendment Dated: April 25, 2007 Reply to Office action of: January 25, 2007

an alternating voltage (34).

6. (Currently Amended) The device according to claim 5, wherein the positioning

means substrate support and/or the substrate (25) are arranged to be electrically

grounded, electrically floating or negatively biased.

7. (Currently Amended) The device according to claim 1, wherein the positioning

means substrate support is a rotating drum (30) and wherein a plurality of magnetron

electrodes (32) having rectangular faces being arranged with their length parallel to

the rotation axis of the drum (30) are arranged around part of a circumference of the

drum (30).

8. (Currently Amended) The device according to claim 7, wherein the gas supply

means comprises gas supply lines (33) extendingextend parallel to the drum axis

between the magnetron faces (20).

(Previously Presented) The device according to claim 7, wherein each of the

plurality of magnetrons (32) is connected to a separate power supply.

10. (Withdrawn) Use of the device according to claim 1 for carrying out a plasma

enhanced chemical vapour deposition process.

(Withdrawn) Use of the device according to claim 1 for depositing silicon oxide

using a process gas comprising an organosilicon compound and oxygen.

Page 4 of 11

Application No.: 10/529531 Amendment Dated: April 25, 2007 Reply to Office action of: January 25, 2007

12. (Withdrawn) Use according to claim 11, wherein the substrate is a web of polymer film material being coated so as to improve barrier properties of said web of polymer film material.